

This listing of claims will replace all prior versions of claims in the application.

Claims 1-79. (cancelled)

Claim 80. (new) A method for forming a photoresist relief image, comprising:

- (a) applying over an integrated circuit substrate a coating layer of an organic antireflective composition that comprises a silsesquioxane resin that comprises one or more optionally substituted anthracene groups;
- (b) applying a coating layer of a photoresist composition over the antireflective composition layer; and
- (c) exposing to patterned radiation and developing the photoresist composition layer to form a photoresist relief image.

Claim 81. (new) The method of claim 80 wherein the photoresist is imaged with radiation having a wavelength of about 248 nm.

Claim 82. (new) The method of claim 80 wherein the antireflective composition further comprises an acid or acid generator compound.

Claim 83. (new) The method of claim 80 wherein the antireflective composition is thermally treated prior to applying the photoresist composition layer.

Claim 84. (new) The method of claim 80 wherein the antireflective composition is crosslinked prior to applying the photoresist composition layer.

Claim 85. (new) The method of claim 80 wherein the antireflective composition is applied over a dielectric layer.

Claim 86. (new) The method of claim 85 wherein the dielectric layer comprises SiO<sub>2</sub>.

Claim 87. (new) The method of claim 85 wherein the dielectric layer comprises an organic resin.